



Name : Devkate . Vijay

Roll no : 2201063

Group : EC31

Lab : VLSI lab

Experiment Title: Input and Output Characteristics of NMOS Using Cadence

1. Objective:

The objective of this experiment is to analyze the input and output characteristics of an NMOS transistor using Cadence Virtuoso. This includes observing the **transfer characteristics (I_d vs. V_{gs})** and **output characteristics (I_d vs. V_{ds})** of the NMOS transistor.

Circuit Design and Setup:

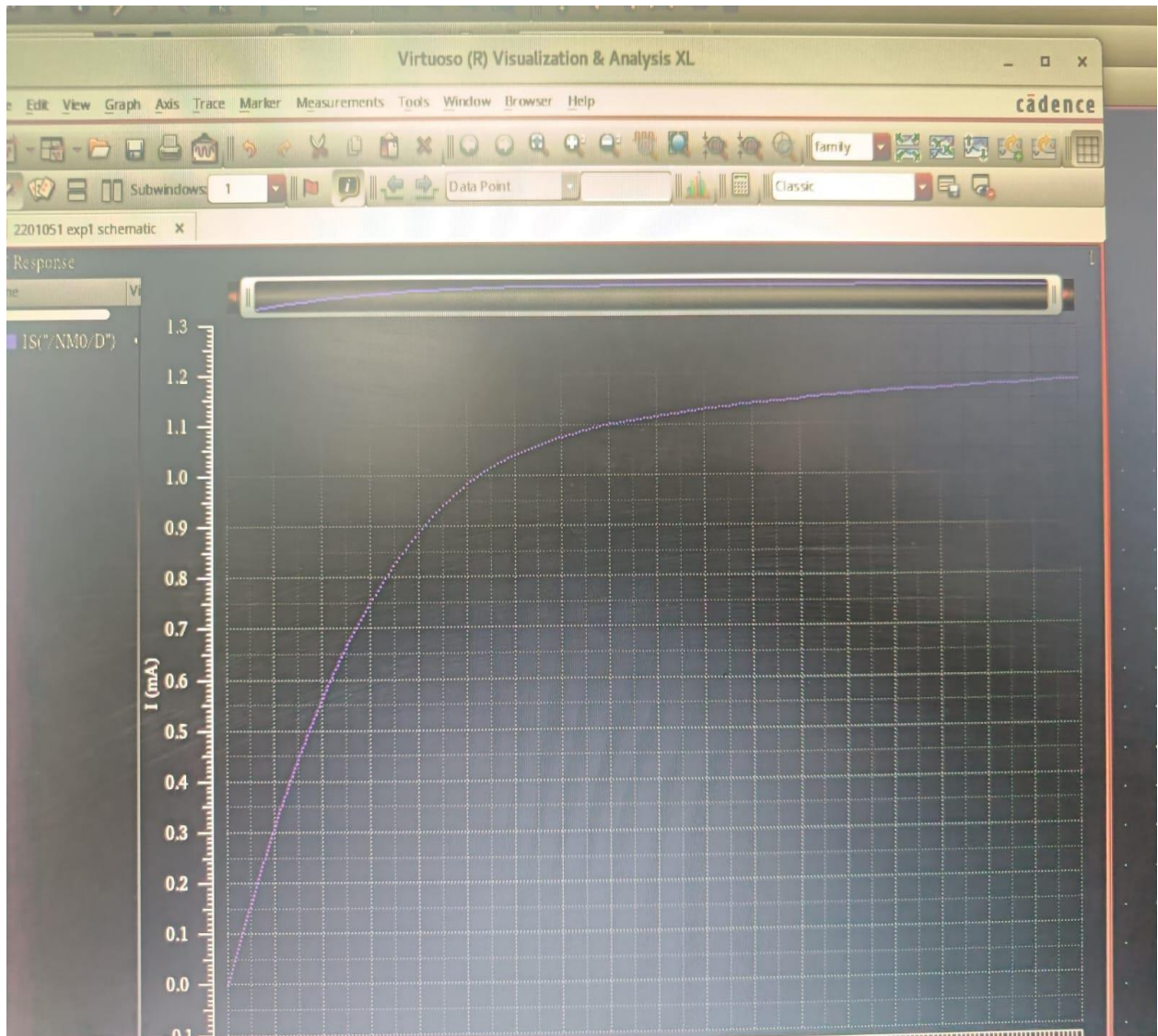
1. Schematic Design:

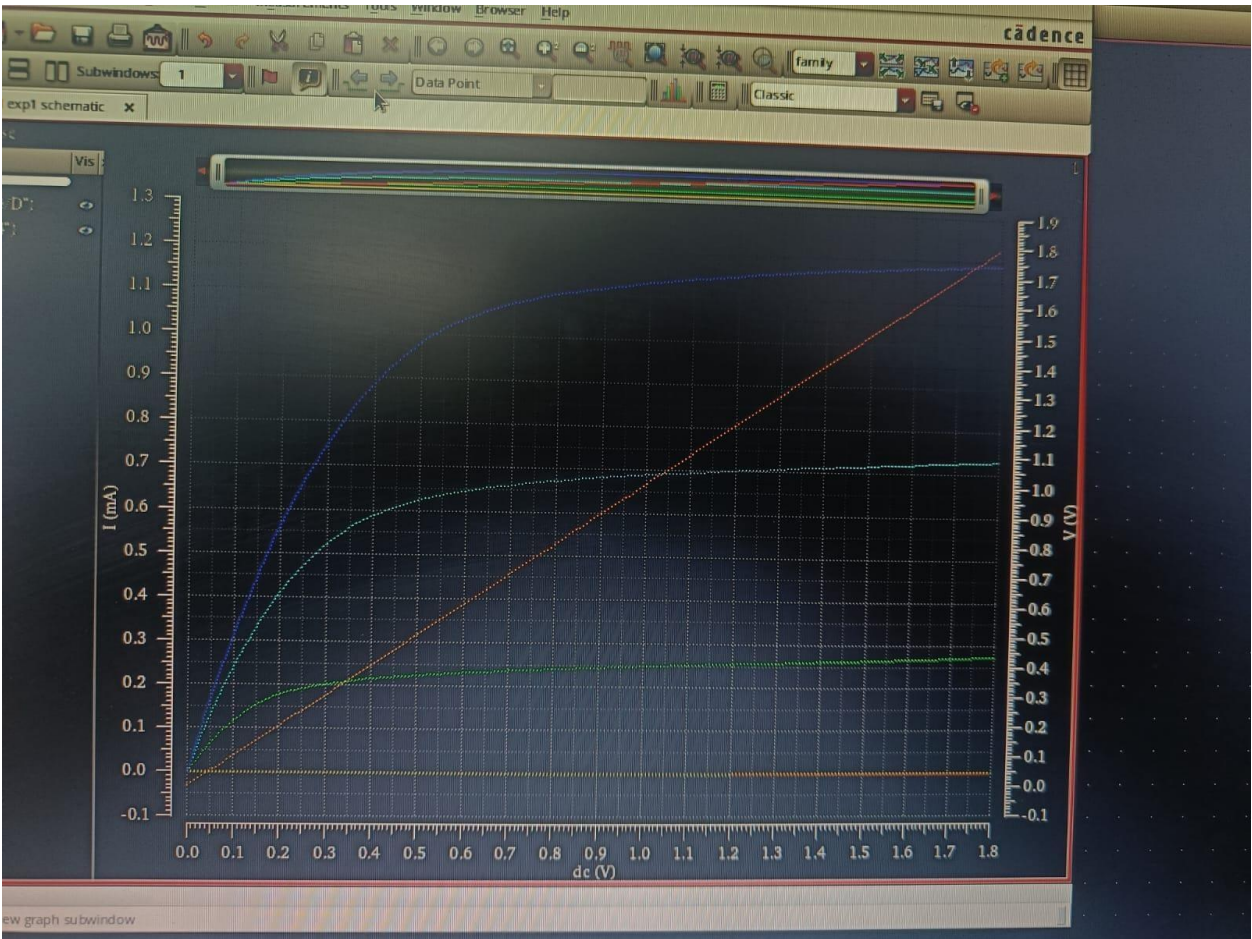
- Open Cadence Virtuoso and create a new schematic.
- Place an NMOS transistor (e.g., from a 180nm/130nm PDK).
- Connect the **drain** to a DC voltage source **V_{ds}** .
- Connect the **gate** to a DC voltage source **V_{gs}** .
- Connect the **source** to **ground (0V)**.
- Place a **current probe** at the drain to measure **I_d** .

2. Simulation Setup:

- Open **ADE-L/XL** and set up a **DC Analysis**.
- For **output characteristics (I_d vs. V_{ds})**:
 - Sweep **V_{ds}** from 0V to a maximum value (e.g., 2V).
 - Set **V_{gs}** at multiple fixed values (e.g., 0.5V, 1V, 1.5V, etc.).
- For **transfer characteristics (I_d vs. V_{gs})**:
 - Sweep **V_{gs}** from 0V to a maximum value (e.g., 2V) while keeping **V_{ds}** fixed (e.g., 1V).
- Run the simulations and save the results.

Results:





Observations:

Output Characteristics (I_d vs. V_{ds}):

- For low V_{ds} , I_d increases linearly, indicating the **ohmic region**.
- As V_{ds} increases, I_d saturates, indicating the **saturation region**.
- Higher V_{gs} values lead to higher I_d , following the MOSFET equations.

Transfer Characteristics (I_d vs. V_{gs}):

- I_d increases exponentially when V_{gs} surpasses the **threshold voltage (V_{th})**.
- The transistor remains **off** for $V_{gs} < V_{th}$.
- I_d follows the quadratic relationship with V_{gs} in the saturation region.

Conclusion:

This experiment successfully demonstrated the input and output characteristics of an NMOS transistor using Cadence Virtuoso. The simulation results validated theoretical MOSFET behavior, with I_d vs. V_{gs} showing a threshold voltage dependency and I_d vs. V_{ds} confirming the transition from the ohmic region to saturation.

Experiment 2: Input and Output Characteristics of PMOS Transistor

Objective

To study and plot the input and output characteristics of a PMOS transistor using Cadence Virtuoso.

Tools Used

- Cadence Virtuoso
- Spectre Simulator
- GPDk 180nm PDK (or your used PDK)

Theory

A PMOS transistor is a type of MOSFET where holes are the majority carriers. It turns **ON** when the gate-to-source voltage V_{GS} is **less than** the threshold voltage V_{th} .

Regions of Operation

1. **Cut-off:** $V_{SG} < V_{th}$
2. **Linear (Triode):** $V_{SD} < V_{SG} - V_{th}$
3. **Saturation:** $V_{SD} \geq V_{SG} - V_{th}$

Schematic Setup

- **PMOS transistor** (from analogLib)
- Connect **source to VDD**, **gate to DC voltage source**, and **drain to VDS sweep source**.

- Bulk tied to source (VDD).

Simulations Performed

1. Output Characteristics (Id vs VSD)

- **Sweep VSD** from 0 to VDD (e.g., 0 to 1.8V)
- **VSG** fixed at multiple values (e.g., 1.2V, 1.5V, 1.8V)

2. Input Characteristics (Id vs VSG) □ Sweep VSG from 0 to VDD

- **VSD** constant (e.g., VSD = 1.8V)

Steps in Cadence Virtuoso

1. **Design the schematic** as per PMOS biasing.
2. **Launch ADE (Analog Design Environment).**
3. Choose **DC analysis**:
 - For output: VSD sweep; VSG as parameter.
 - For input: VSG sweep; VSD constant.
4. Run simulation.
5. Use **Calculator** or direct plotting to plot Id vs VSD and Id vs VSG.
6. Annotate curves and export graphs.

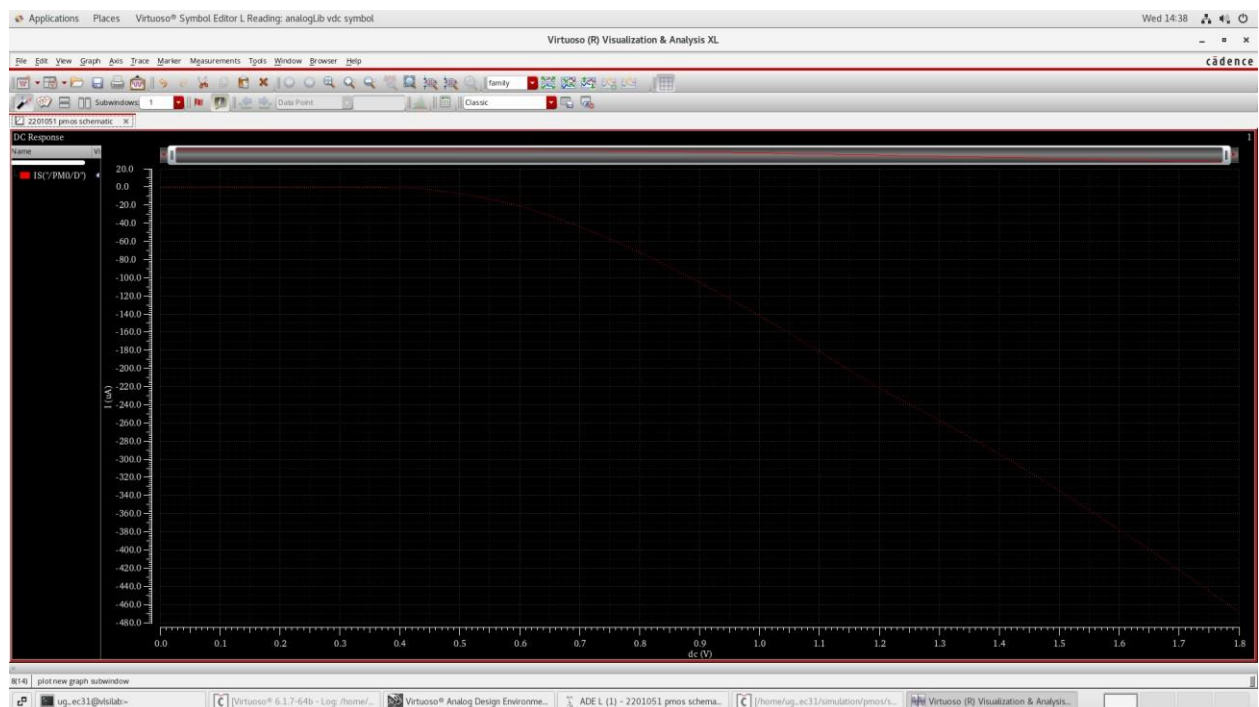
Results

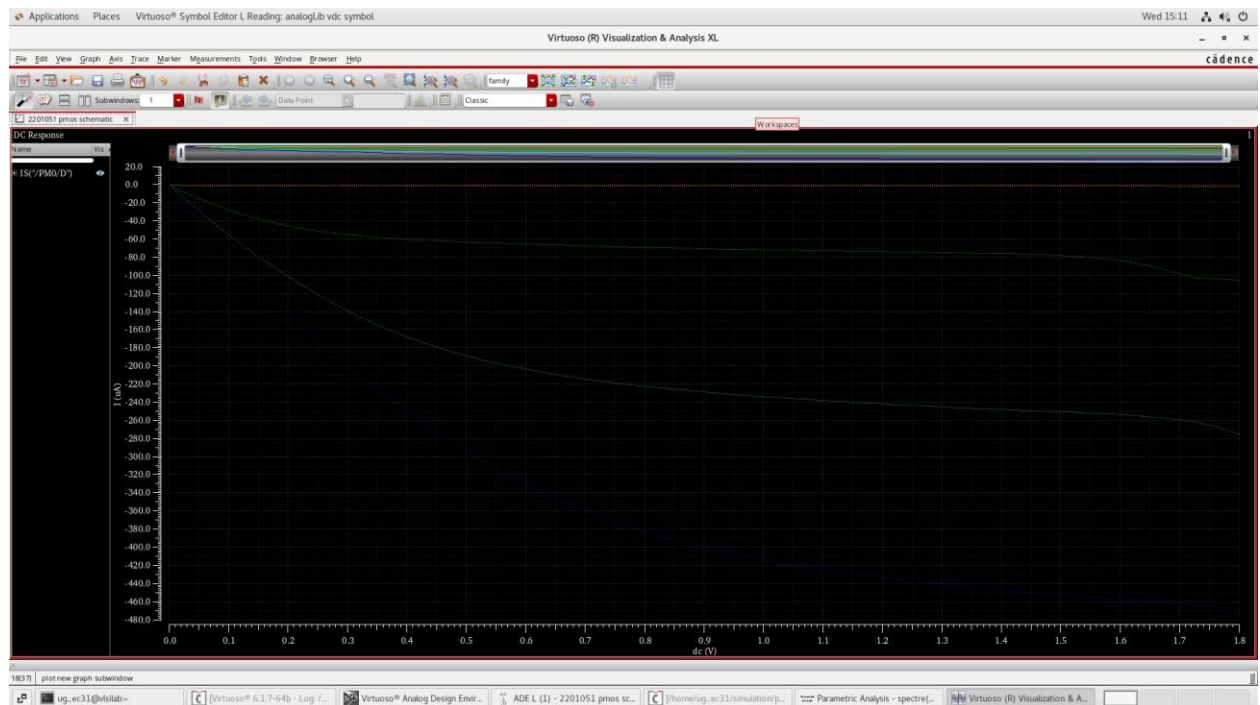
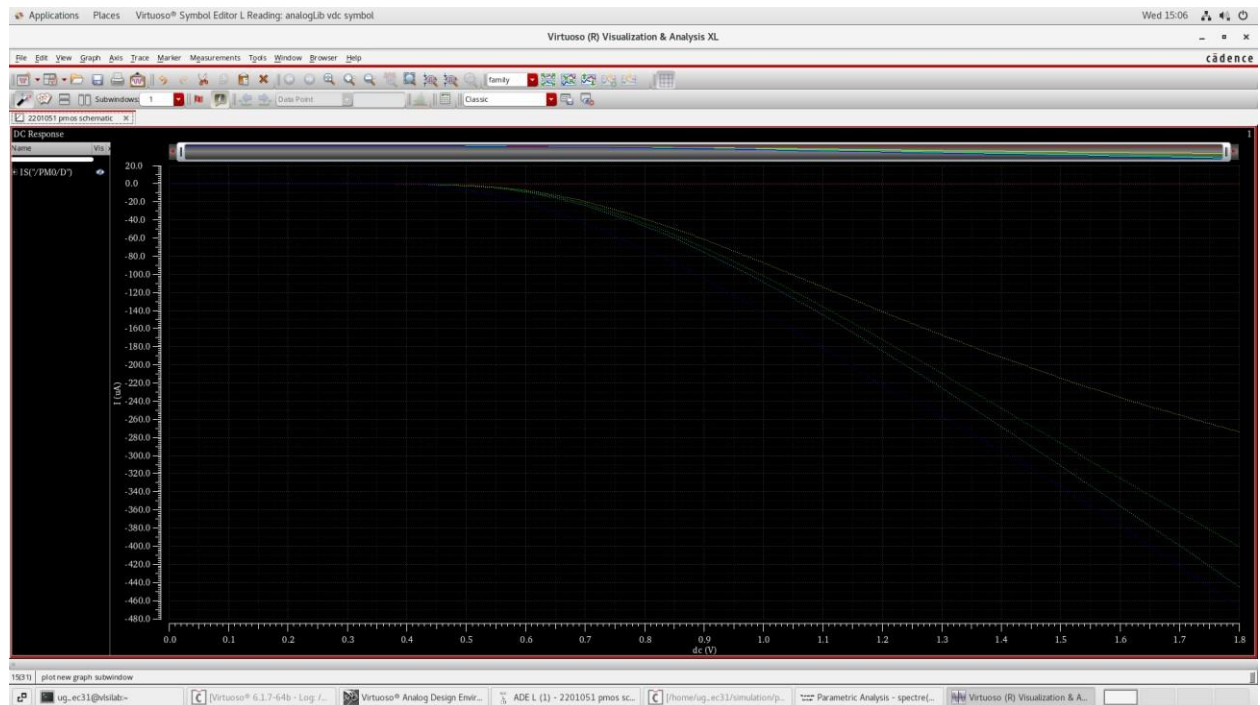
Output Characteristics

- I_d increases with VSD initially (linear region), then saturates.
- Higher VSG (more negative gate voltage) increases I_d .

Input Characteristics

- I_d increases exponentially when VSG increases past threshold ($\sim 0.5V$).
- Very low current for $V_{SG} < V_{th}$.





Conclusion

- PMOS operates in three regions depending on V_{SG} and V_{SD} .
- The characteristics confirm expected PMOS behavior.
- Simulations match theoretical behavior of PMOS.

Observations

- Threshold voltage $V_{th} \sim -0.5V$ for the PMOS in this PDK.
- PMOS conducts when gate is at lower potential than source.

Experiment 3: Gain and Phase Response of Common Source Amplifier

Objective

To analyze the **gain** and **phase response** of a **Common Source (CS) Amplifier** using Cadence Virtuoso.

Tools Used

- Cadence Virtuoso
- Spectre Simulator
- GPDK 180nm PDK (or the PDK you are using)

Theory

The **Common Source amplifier** is a basic analog amplifier configuration using an NMOS transistor. It provides:

- **High voltage gain**
- **180° phase shift** between input and output

Voltage Gain

$$A_v = -g_m R_{D_v} = -g_m R_{D_D}$$

Where:

- g_m = transconductance
- R_{D_D} = drain resistance

The negative sign indicates a **phase inversion**.

Schematic Setup

- **NMOS transistor** (from analogLib) □ **Biasing:**

- Gate: connected through a resistor to DC voltage (bias) ○ Source: grounded
- Drain: connected to VDD through resistor RDR_D
- **Input:** small AC signal superimposed on gate bias
- **Output:** taken from the drain

Simulation Configuration

1. AC Analysis (Gain & Phase)

- Sweep frequency: 1Hz to 1GHz (log scale)
- AC magnitude: 1V at input (for easy gain reading)

Steps in Cadence Virtuoso

1. **Draw the CS amplifier schematic** with proper biasing.
2. **Launch ADE.**
3. **Set up AC analysis:**
 - AC input source with magnitude 1V
 - Sweep frequency: 1Hz to 1GHz (decade sweep, 10 points/decade)
- 4.

Run simulation

5. Use **Calculator:**
 - Gain: $v(out)/v(in)$
 - Gain in dB: $20 \cdot \log_{10}(mag(...))$ ○ Phase: $phase(...)$
6. Plot and annotate.

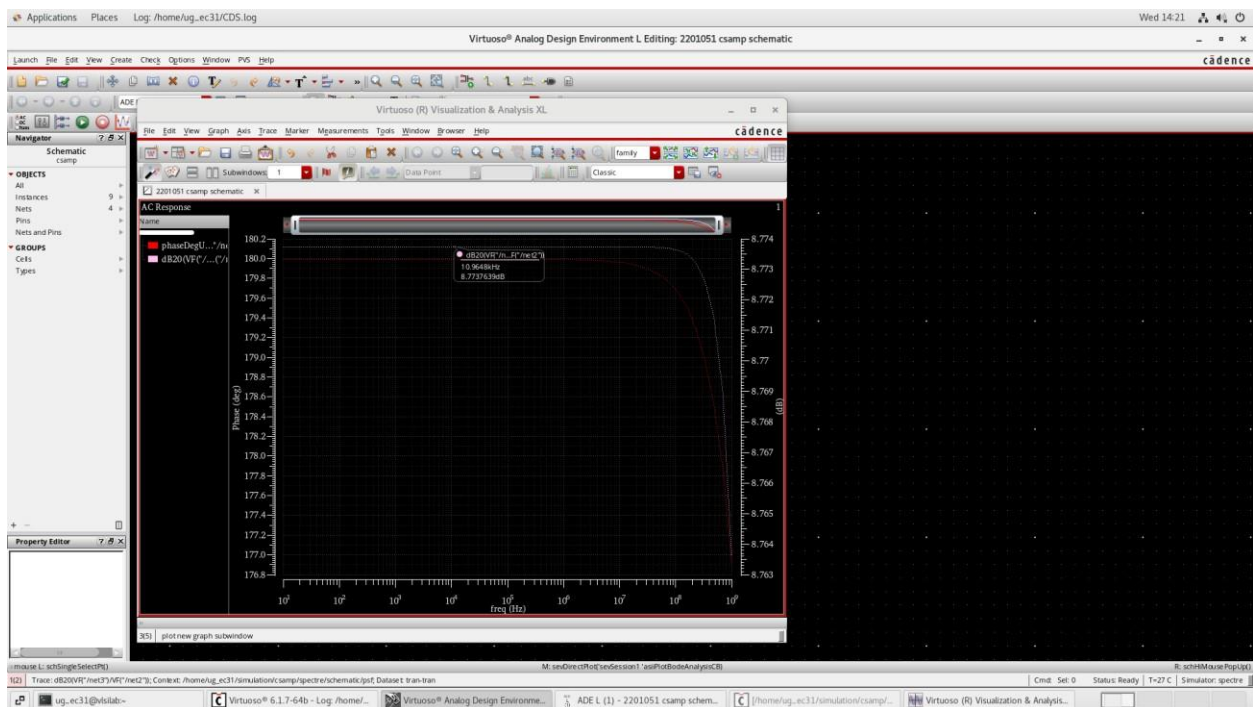
Results

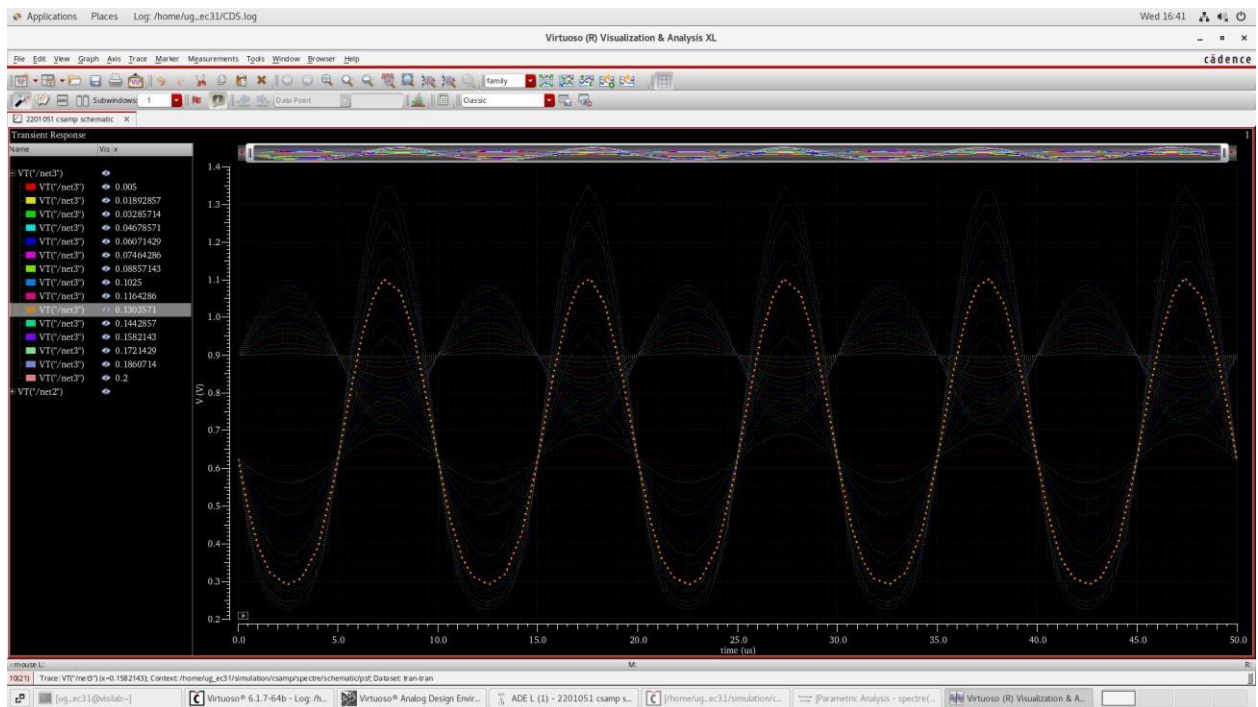
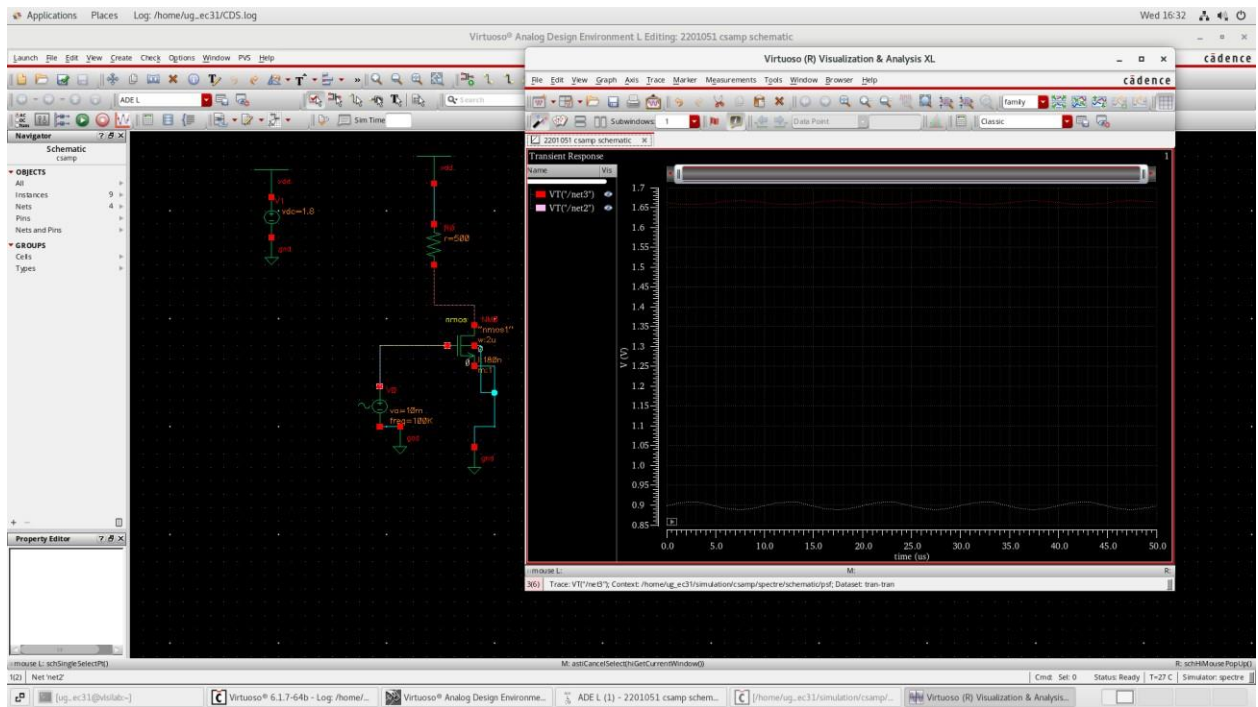
Gain Plot

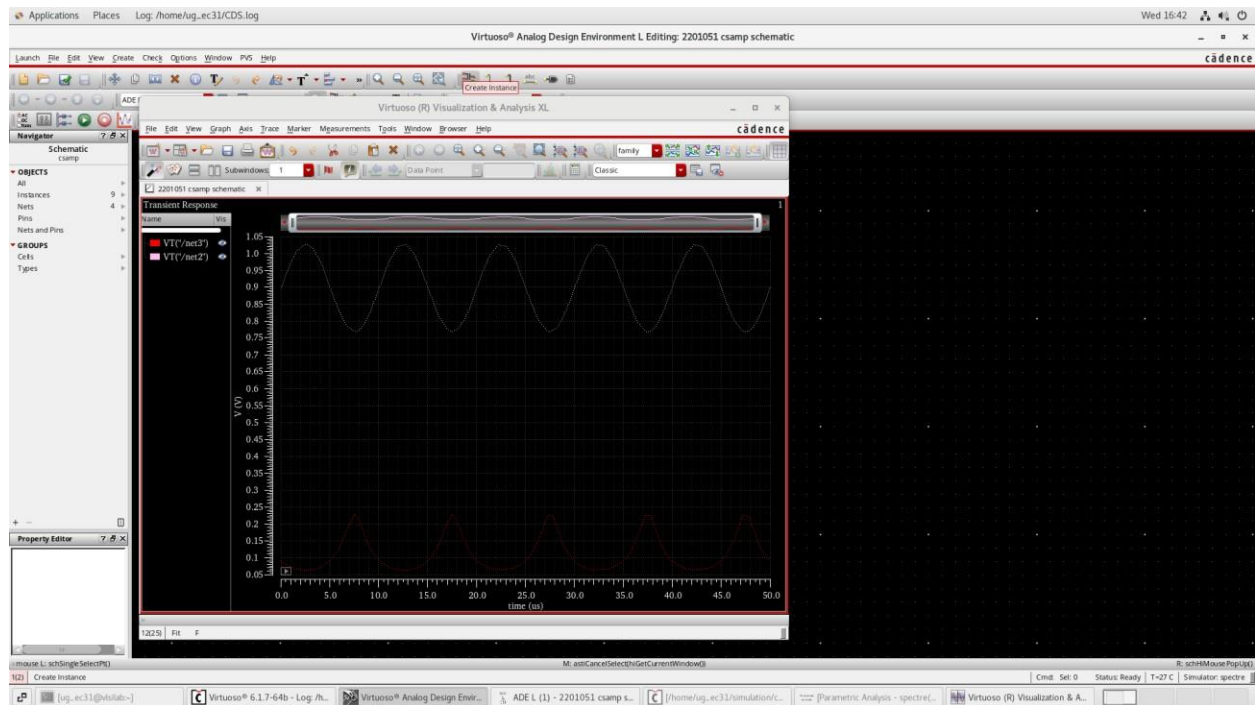
- Midband gain is approximately constant.
- Low gain at very low and very high frequencies due to coupling and parasitic capacitances.

Phase Plot

- Phase shift is around -180° in midband.
- Shows typical low-pass phase behavior at high frequencies.







Conclusion

- The CS amplifier exhibits a significant voltage gain in midband frequency.
- Phase shift confirms the inverting nature ($\sim 180^\circ$).
- Frequency response matches expected behavior of a single-stage CS amplifier.

Observations

- **3-dB bandwidth** indicates the frequency range over which gain is nearly constant.
- **Miller effect** limits high-frequency performance.
- Gain depends on transistor parameters and load resistance.

Experiment 4: DC Input-Output Characteristics of CMOS Inverter

Objective

To obtain and analyze the **DC transfer characteristics** of a **CMOS inverter** using Cadence Virtuoso.

Tools Used

- Cadence Virtuoso
- Spectre Simulator
- GPDK 180nm PDK

Theory

A **CMOS inverter** is built using a PMOS and an NMOS transistor:

- **PMOS**: Source connected to **VDD**
- **NMOS**: Source connected to **GND**
- Gates tied together: **input**
- Drains tied together: **output**
- **Working Principle**
- **$V_{in} = 0$** → PMOS ON, NMOS OFF → **$V_{out} = VDD$**
- **$V_{in} = VDD$** → PMOS OFF, NMOS ON → **$V_{out} = 0$**
- **$V_{in} = VDD/2$** → both transistors partially ON → transition region

Schematic Setup

- PMOS and NMOS connected in inverter configuration
- Input connected to DC voltage source (V_{in})
- Output taken at common drain node
- PMOS bulk connected to VDD, NMOS bulk to GND

Simulation Configuration

DC Sweep Analysis

- Sweep **Vin** from 0 to VDD (e.g., 0 to 1.8V)
- Measure **Vout** across the same sweep
- Plot **Vout vs Vin**

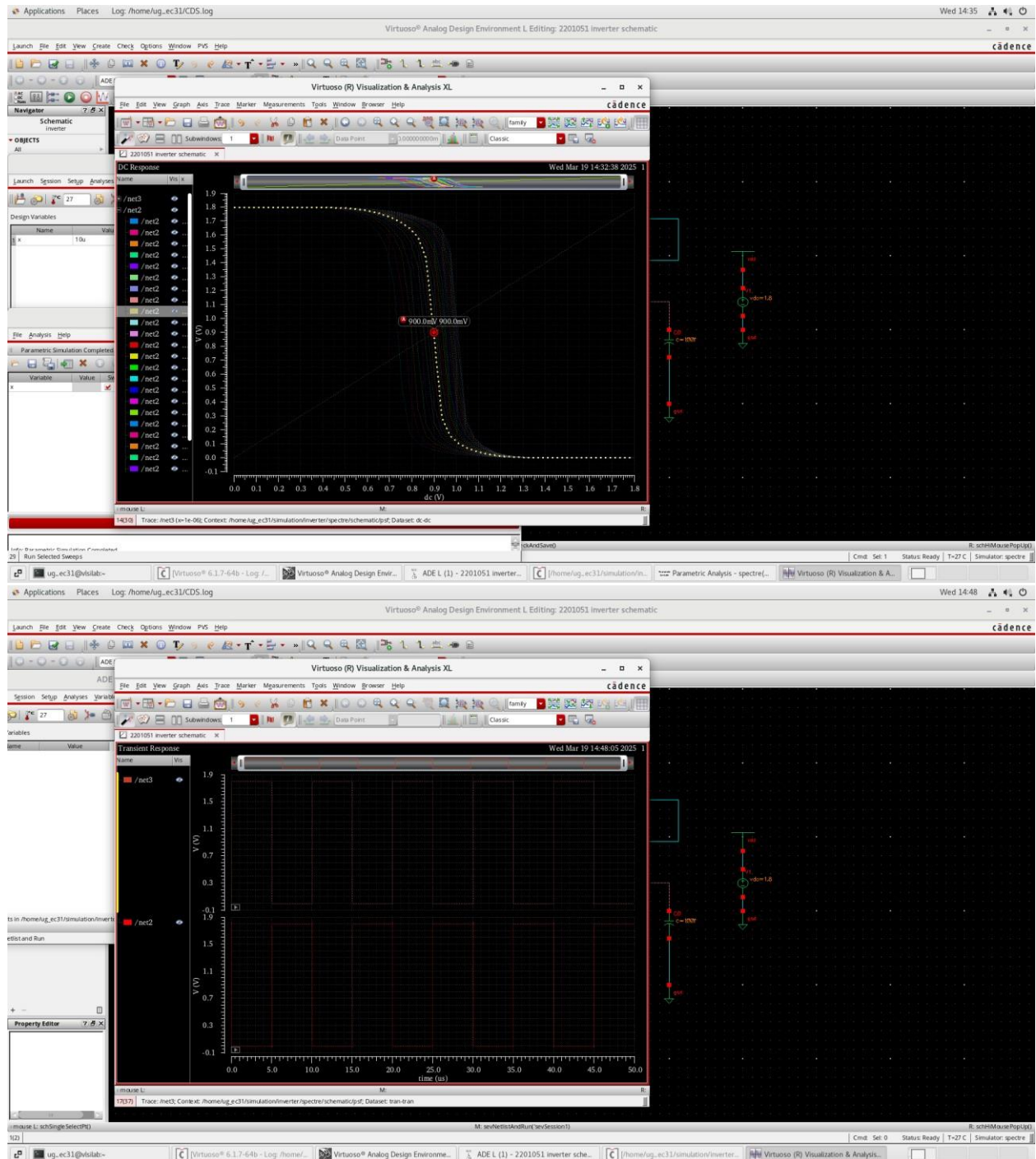
Steps in Cadence Virtuoso

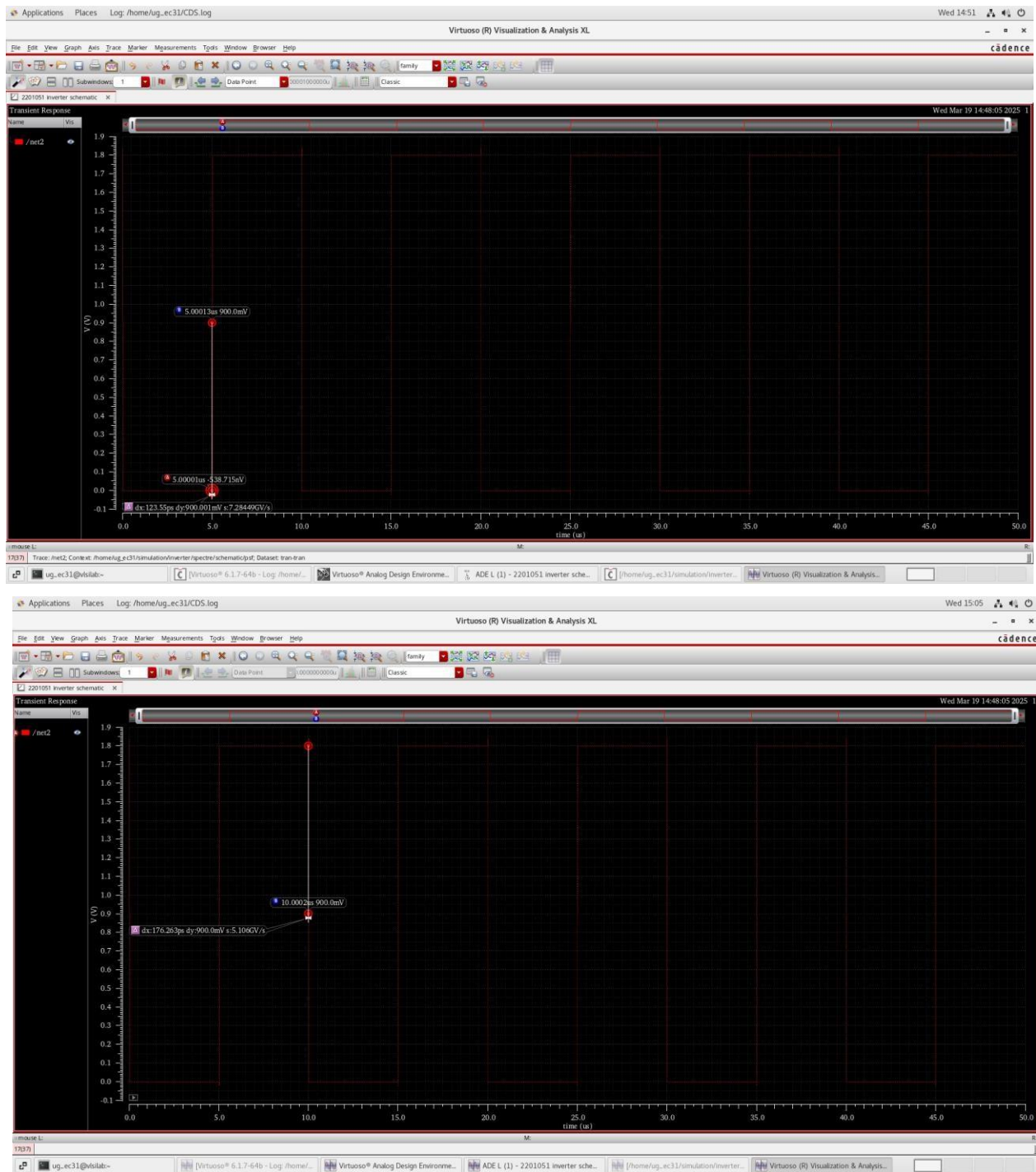
1. Draw **schematic** of CMOS inverter.
2. Connect:
 - Vin to gate of both transistors (sweep source)
 - Vout from common drain
 - VDD = 1.8V (or as per PDK), GND = 0V
3. Launch **ADE (Analog Design Environment)**.
4. Select **DC sweep**: ◦ Sweep Vin from 0V to 1.8V (or your VDD)
5. Run simulation.
6. Plot **Vout vs Vin**.

Results

- **Vout vs Vin** plot shows sharp transition.

- Transition point $\approx VDD/2$
- Confirms inverter behavior.





Conclusion

- The CMOS inverter exhibits expected switching characteristics.

- Output is high when input is low and vice versa.
- Sharp transition region observed, indicating high gain during switching.

Observations

- **Noise margins** can be estimated from the curve.
- The inverter acts as a NOT gate with rail-to-rail swing.

Experiment 5: NAND Gate Using CMOS (NMOS and PMOS) – Truth Table Verification

Objective

To implement a 2-input NAND gate using NMOS and PMOS transistors and verify its truth table using DC analysis in Cadence Virtuoso.

Tools Used

- **Cadence Virtuoso**
- **Spectre Simulator**
- **GPDK 180nm PDK (or your available PDK)**

Theory

A CMOS NAND gate uses:

- Two PMOS transistors in parallel at the pull-up network.

- Two NMOS transistors in series at the pull-down network.

A B Y (NAND)

0 0 1

0 1 1

1 0 1

1 1 0

Schematic Setup

- Pull-up network:
 - Two PMOS transistors in parallel
 - Sources connected to VDD
 - Drains connected to output
 - Gates: connected to A and B
- Pull-down network:
 - Two NMOS transistors in series
 - Drain of first to output
 - Source of second to GND
 - Gates: connected to A and B
- Inputs: A and B (DC voltage sources)
- Output: Common connection between pull-up and pull-down

Simulation Configuration

DC Sweep (Truth Table Verification)

- Apply all four input combinations: ○ A = 0/1V, B = 0/1V (or 0/1.8V if using 1.8V VDD)
- Observe Vout for each case
- Compare with expected NAND truth table

Steps in Cadence Virtuoso

1. Design CMOS NAND gate schematic using PMOS and NMOS from analogLib
2. Add two DC sources: A and B
3. Connect output node to a wire label out
4. In ADE:
 - Use DC sweep with nested sweeps:
 - Sweep A: 0V to VDD
 - Sweep B: 0V to VDD
 - Or manually set A and B to all 4 combinations using Design Variables & parametric sweep
5. Run simulation
6. Plot Vout vs input combinations or check from results table

Results

A B Vout (Simulated) Logic Level

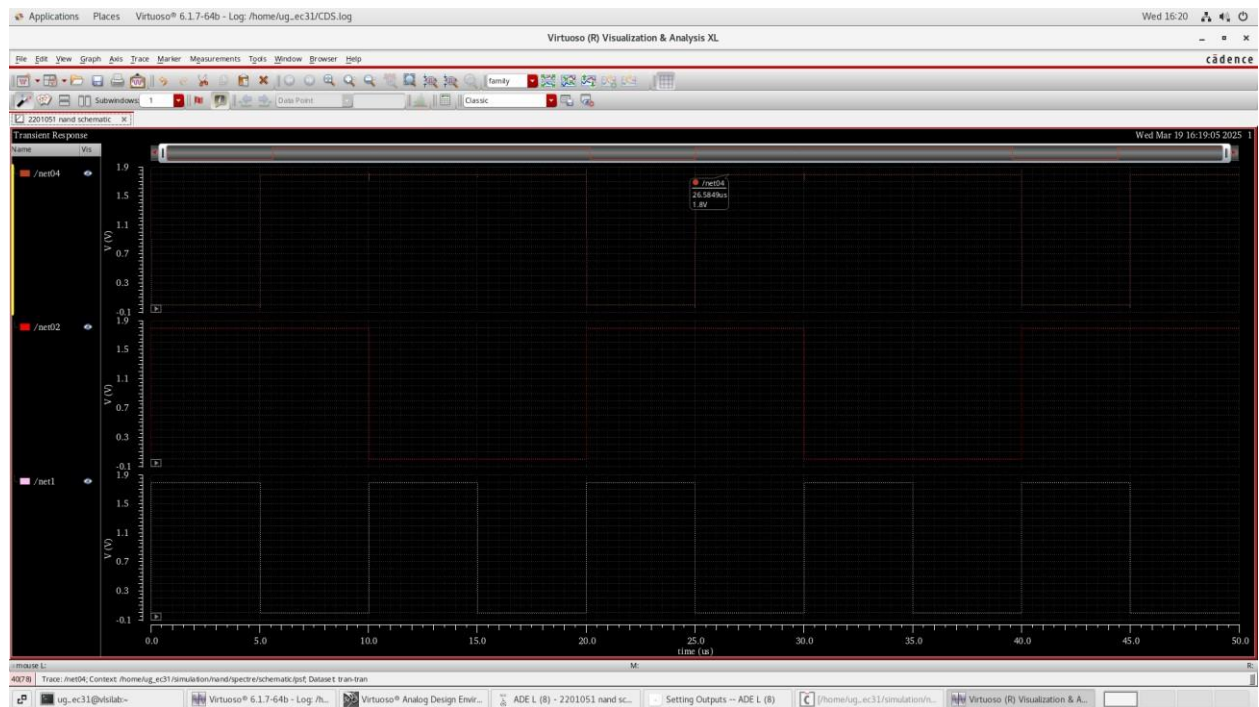
0 0 ~VDD (1.8V) 1

0 1 ~VDD (1.8V) 1

1 0 ~VDD (1.8V) 1

1 1 ~0V

0



Conclusion

- The CMOS NAND gate behaves as expected.
- The output goes LOW only when both inputs are HIGH.
- Truth table is verified successfully using DC simulation.

Observations

- PMOS transistors are ON when input is LOW
- NMOS transistors are ON when input is HIGH
- CMOS logic ensures low static power consumption and sharp transitions

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Experiment 6: **NOR Gate Using CMOS (NMOS and PMOS) – Truth Table Verification**

Objective

To design and simulate a **2-input NOR gate** using **CMOS technology** (NMOS and PMOS transistors) and verify its **truth table** in **Cadence Virtuoso** using DC analysis.

Tools Used

- Cadence Virtuoso
- Spectre Simulator
- GPDK 180nm PDK

Theory

A **CMOS NOR gate** is built using:

- **PMOS transistors in series** for the **pull-up network**
- **NMOS transistors in parallel** for the **pull-down network**

A B Y (NOR)

0 0 1

0 1 0

1 0 0

1 1 0

Schematic Setup

- **Pull-up network (PMOS in series):**
 - Sources: connected to VDD
 - Drains: connected together to output
 - Gates: A and B
 - Middle connection between PMOS transistors
- **Pull-down network (NMOS in parallel):**
 - Drains: connected together to output
 - Sources: to GND
 - Gates: A and B
- **Inputs:** A and B (DC voltage sources)
- **Output:** Taken from node where pull-up and pull-down networks meet

Simulation Configuration

DC Sweep (Truth Table Verification)

- Apply all combinations of A and B:
 - A = 0V or VDD, B = 0V or VDD (e.g., VDD = 1.8V)
- Observe **Vout** for each case
- Compare results with expected **NOR truth table**

Steps in Cadence Virtuoso

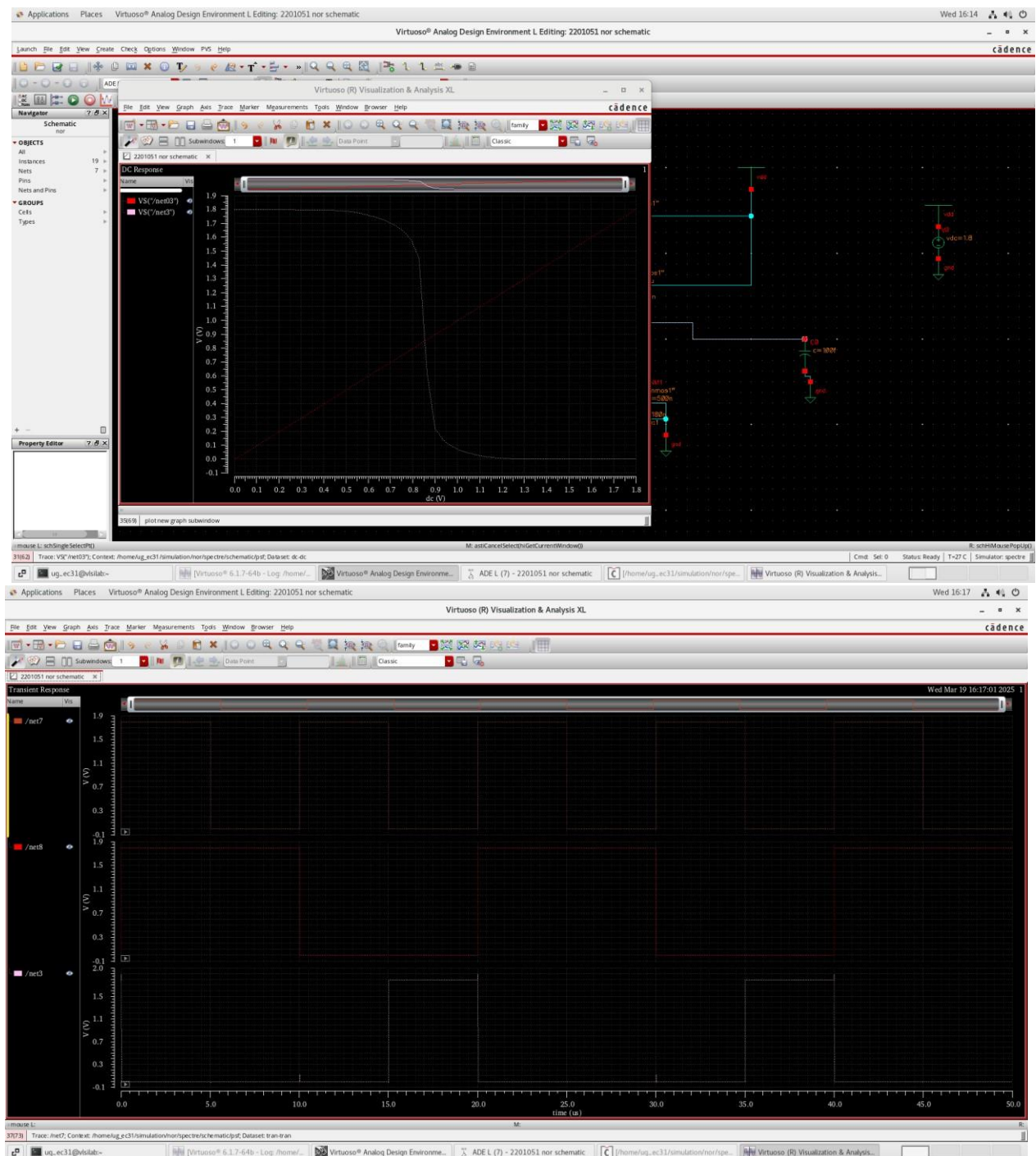
1. **Build CMOS NOR gate** using PMOS (series) and NMOS (parallel)

2. Use **DC voltage sources** for A and B inputs
3. Output node labeled as out
4. In **ADE**:
 - Set **Design Variables** for A and B
 - Run **DC parametric sweep** over combinations:
 - A: 0, 1.8V
 - B: 0, 1.8V
5. Simulate and observe **Vout** for each combination

Results

A B Vout (Simulated) Logic Level

0 0 ~VDD (1.8V)	1
0 1 ~0V	0
1 0 ~0V	0
1 1 ~0V	0



Conclusion

- The CMOS NOR gate functions correctly.
- Output is **HIGH** only when **both inputs are LOW**
- Truth table matches theoretical NOR logic behavior

Observations

- **PMOS** turns ON when input is LOW
- **NMOS** turns ON when input is HIGH
- **Series PMOS** ensures output is HIGH only when both inputs are LOW □

CMOS design gives **low power** and **full-swing output**

Experiment 7: D Flip-Flop Functional Verification with 20% and 25% Clock Duty Cycles

Objective

To design a **D Flip-Flop (DFF)** using CMOS logic and verify its correct behavior with **non-standard clock duty cycles** of **20%** and **25%** using transient simulation in **Cadence Virtuoso**.

Tools Used

- Cadence Virtuoso
- Spectre Simulator
- GPDK 180nm PDK (or your PDK)

Theory

A **D Flip-Flop** (positive-edge triggered) transfers input D to output Q on the **rising edge** of the clock (CLK).

Truth Table

CLK (↑) D Q (next)

Rising 0 0

Rising 1 1

Else x Hold

Duty Cycle

- 20% duty cycle → clock HIGH for 20% of one period
- 25% duty cycle → clock HIGH for 25% of one period

Schematic Setup

- Use : ◦ Custom-built CMOS DFF (master-slave latch) ◻ Inputs:
 - D: pulse or square wave
 - CLK:
pulse source with:
 - 20% duty cycle
 - 25% duty cycle
- Output: Q

Simulation Configuration

Transient Analysis

- Time: 0 to e.g. 500ns ◻ Input D: toggling every 50ns
- CLK:
 - **20% duty** ◦ **25% duty** ◻ Observe:
 - Output Q changes only on rising edges
 - Q holds value otherwise

Steps in Cadence Virtuoso 1. Create

D Flip-Flop schematic.

2. Add:

- **Pulse source** for CLK (adjust duty) ○
- Pulse or square source** for D

3. Set up **transient simulation**:

- Run time: ~500ns

4. Plot D, CLK, and Q.

Repeat simulation with:

- Clock duty cycle = **20%**
- Clock duty cycle = **25%**

Results

Case 1: 20% Duty Cycle

- CLK HIGH for 20ns every 100ns
- Q changes at rising edge
- Q holds otherwise



Case 2: 25% Duty Cycle

- CLK HIGH for 25ns every 100ns
- Q again changes at rising edge only



Conclusion

- The D Flip-Flop **correctly samples D at CLK rising edges**, even under **low duty cycles (20% and 25%)**
- Output Q remains **stable** between edges, confirming **edge-triggered** behavior

Observations

- Duty cycle affects **timing margin** and setup/hold time constraints
- Even with low duty cycle, as long as **rise edge is defined**, DFF functions properly

Experiment 8: Current Mirror Design and Verification in Cadence Virtuoso

Objective

To design and simulate a **basic current mirror** using **NMOS transistors** in **Cadence Virtuoso**, and verify that the output current mirrors the reference current.

Tools Used

- Cadence Virtuoso
- Spectre Simulator
- GPDK 180nm PDK

Theory

A **current mirror** copies a reference current (I_{REF}) to an output branch using matched transistors. It's widely used in analog ICs for biasing and current control.

Basic NMOS Current Mirror

- **M1**: Diode-connected NMOS (gate and drain shorted)

- **M2**: Output transistor, gate tied to M1's gate
- Both sources connected to **GND**
- Same **W/L ratios** ensure mirrored current:

$$I_{OUT} = I_{REF} \quad I_{OUT} = I_{REF}$$

Schematic Setup

- **M1**: Gate and drain connected, reference current sourced via I_{REF}
- **M2**: Gate connected to M1's gate, drain is output
- Connect both sources to GND
- **Power supply**: $V_{DD} = 1.8V$
- Use **ideal current source** or **resistor from VDD to drain of M1** to set I_{REF}

Simulation Configuration DC

Analysis

- Sweep **Vout (M2's drain)** from 0 to V_{DD}
- Observe **Iout** as Vout changes
- Expect constant current when **M2 is in saturation**

Steps in Cadence Virtuoso

1. Draw **basic NMOS current mirror** schematic.
2. Set **M1 and M2** to same W/L (e.g., $W = 2\mu$, $L = 180nm$)
3. Apply I_{REF} via current source or resistor
4. Sweep **Vout** via DC voltage source
5. In **ADE**, choose **DC sweep**:

- Sweep V_{out} from 0 to 1.8V

6. Plot I_{out} vs V_{out}

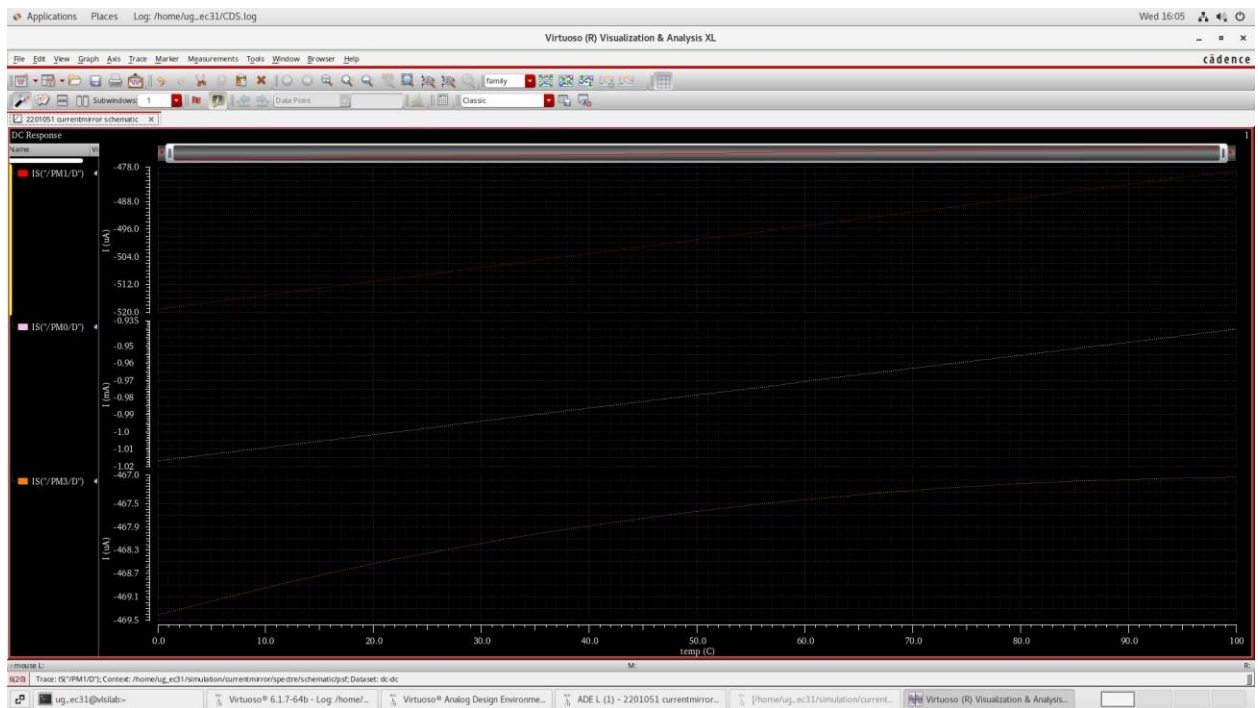
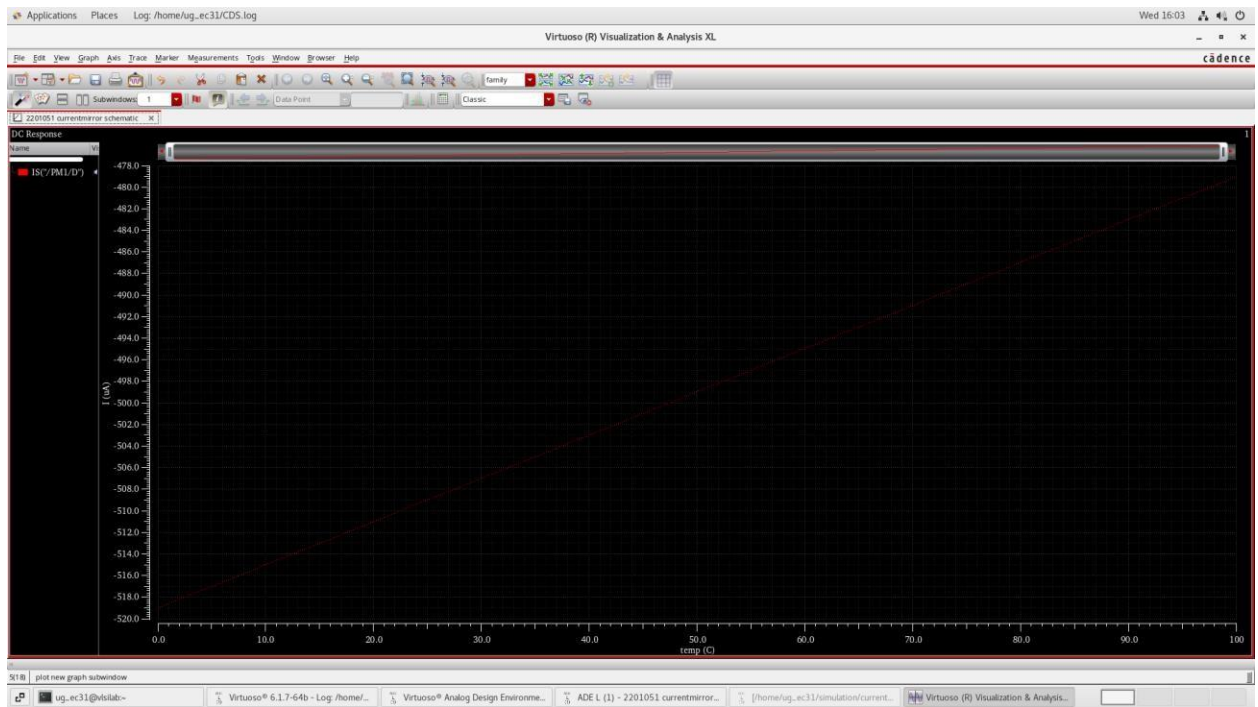
Results

Expected Behavior

- For $V_{out} > V_{dsat}$, **M2** stays in saturation
- $I_{out} \approx I_{ref}$ (flat region in plot)

Plot

- X-axis: V_{out} (M2's drain)
- Y-axis: I_{out} (drain current of M2)
- Flat region confirms **current mirroring**



Conclusion

- The current mirror successfully replicates I_{REF} at the output
- I_{out} remains **constant over a range of V_{out}** , indicating M2 stays in **saturation**
- Confirms proper current mirror operation

Observations

- Matching W/L is crucial for accurate mirroring □ V_{out} must be high enough to keep M2 in saturation □ Can scale current by adjusting W/L of M2: